



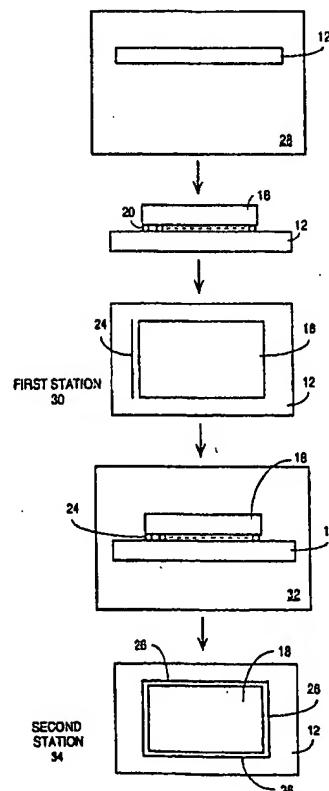
INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification ⁷: H01L 21/56, 23/18, 23/24	A1	(11) International Publication Number: WO 00/52751 (43) International Publication Date: 8 September 2000 (08.09.00)
(21) International Application Number: PCT/US00/03243 (22) International Filing Date: 8 February 2000 (08.02.00) (30) Priority Data: 09/262,132 3 March 1999 (03.03.99) US (71) Applicant (for all designated States except US): INTEL CORPORATION [US/US]; 2200 Mission College Boulevard, Santa Clara, CA 95052 (US). (72) Inventors; and (75) Inventors/Applicants (for US only): COOK, Duane [US/US]; 1520 San Andreas Avenue, San Jose, CA 95118 (US). RAMALINGAM, Suresh [IN/US]; 34276 Dunhill Drive, Fremont, CA 94555 (US). (74) Agents: MILLIKEN, Darren, J. et al.; Blakely, Sokoloff, Taylor & Zafman LLP, 7th floor, 12400 Wilshire Boulevard, Los Angeles, CA 90025 (US).		(81) Designated States: AE, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, CA, CH, CN, CR, CU, CZ, DE, DK, DM, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZW, ARIPO patent (GH, GM, KE, LS, MW, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG). Published <i>With international search report.</i>

(54) Title: A PROCESS LINE FOR UNDERFILLING A CONTROLLED COLLAPSE CHIP CONNECTION (C4) INTEGRATED CIRCUIT PACKAGE

(57) Abstract

A high throughput process line and method for underfilling an integrated circuit that is mounted to a substrate. The process line includes a first dispensing station that dispenses a first underfill material onto the substrate and an oven which moves the substrate while the underfill material flows between the integrated circuit and the substrate. The process line removes flow time (wicking time) as the bottleneck for achieving high throughput.



FOR THE PURPOSES OF INFORMATION ONLY

Codes used to identify States party to the PCT on the front pages of pamphlets publishing international applications under the PCT.

AL	Albania	ES	Spain	LS	Lesotho	SI	Slovenia
AM	Armenia	FI	Finland	LT	Lithuania	SK	Slovakia
AT	Austria	FR	France	LU	Luxembourg	SN	Senegal
AU	Australia	GA	Gabon	LV	Latvia	SZ	Swaziland
AZ	Azerbaijan	GB	United Kingdom	MC	Monaco	TD	Chad
BA	Bosnia and Herzegovina	GE	Georgia	MD	Republic of Moldova	TG	Togo
BB	Barbados	GH	Ghana	MG	Madagascar	TJ	Tajikistan
BE	Belgium	GN	Guinea	MK	The former Yugoslav Republic of Macedonia	TM	Turkmenistan
BF	Burkina Faso	GR	Greece			TR	Turkey
BG	Bulgaria	HU	Hungary	ML	Mali	TT	Trinidad and Tobago
BJ	Benin	IE	Ireland	MN	Mongolia	UA	Ukraine
BR	Brazil	IL	Israel	MR	Mauritania	UG	Uganda
BY	Belarus	IS	Iceland	MW	Malawi	US	United States of America
CA	Canada	IT	Italy	MX	Mexico	UZ	Uzbekistan
CF	Central African Republic	JP	Japan	NE	Niger	VN	Viet Nam
CG	Congo	KE	Kenya	NL	Netherlands	YU	Yugoslavia
CH	Switzerland	KG	Kyrgyzstan	NO	Norway	ZW	Zimbabwe
CI	Côte d'Ivoire	KP	Democratic People's Republic of Korea	NZ	New Zealand		
CM	Cameroon			PL	Poland		
CN	China	KR	Republic of Korea	PT	Portugal		
CU	Cuba	KZ	Kazakstan	RO	Romania		
CZ	Czech Republic	LC	Saint Lucia	RU	Russian Federation		
DE	Germany	LI	Liechtenstein	SD	Sudan		
DK	Denmark	LK	Sri Lanka	SE	Sweden		
EE	Estonia	LR	Liberia	SG	Singapore		

-1-

**A PROCESS LINE FOR UNDERFILLING A CONTROLLED COLLAPSE
CHIP CONNECTION (C4) INTEGRATED CIRCUIT PACKAGE**

BACKGROUND OF THE INVENTION

1. FIELD OF THE INVENTION

The present invention relates to an integrated circuit package.

2. BACKGROUND INFORMATION

Integrated circuits are typically assembled into a package that is soldered to a printed circuit board. Figure 1 shows a type of integrated circuit package that is commonly referred to as flip chip or C4 package. The integrated circuit 1 contains a number of solder bumps 2 that are soldered to a top surface of a substrate 3.

The substrate 3 is typically constructed from a composite material which has a coefficient of thermal expansion that is different than the coefficient of thermal expansion for the integrated circuit. Any variation in the temperature of the package may cause a resultant differential expansion between the integrated circuit 1 and the substrate 3. The differential expansion may induce stresses that can crack the solder bumps 2. The solder bumps 2 carry electrical current

-2-

between the integrated circuit 1 and the substrate 3 so that any crack in the bumps 2 may affect the operation of the circuit 1.

The package may include an underfill material 4 that is located between the integrated circuit 1 and the substrate 3. The underfill material 4 is typically an epoxy which strengthens the solder joint reliability and the thermo-mechanical moisture stability of the IC package.

The package may have hundreds of solder bumps 2 arranged in a two dimensional array across the bottom of the integrated circuit 1. The epoxy 4 is typically applied to the solder bump interface by dispensing a single line of uncured epoxy material along one side of the integrated circuit. The epoxy then flows between the solder bumps. The epoxy 4 must be dispensed in a manner that covers all of the solder bumps 2.

It is desirable to dispense the epoxy 4 at only one side of the integrated circuit to insure that air voids are not formed in the underfill. Air voids weaken the structural integrity of the integrated circuit/substrate interface. Additionally, the underfill material 4 must have good adhesion strength with both the substrate 3 and the integrated circuit 1 to prevent delamination during thermal and moisture loading. The epoxy 4 must therefore be a material which is provided in a state that can flow under the entire integrated circuit/substrate interface while having good adhesion properties.

-3-

The substrate 3 is typically constructed from a ceramic material. Ceramic materials are relatively expensive to produce in mass quantities. It would therefore be desirable to provide an organic substrate for a C4 package. Organic substrates tend to absorb moisture which may be released during the underfill process. The release of moisture during the underfill process may create voids in the underfill material. Organic substrates also tend to have a higher coefficient of thermal expansion compared to ceramic substrates that may result in higher stresses in the die, underfill and solder bumps. The higher stresses in the epoxy may lead to cracks during thermal loading which propagate into the substrate and cause the package to fail by breaking metal traces. The higher stresses may also lead to die failure during thermal loading and increase the sensitivity to air and moisture voiding. The bumps may extrude into the voids during thermal loading, particularly for packages with a relatively high bump density. It would be desirable to provide a C4 package that utilizes an organic substrate.

SUMMARY OF THE INVENTION

One embodiment of the present invention is a process line and method for underfilling an integrated circuit that is mounted to a substrate. The process line includes a first dispensing station that dispenses

-4-

a first underfill material onto the substrate and an oven which moves the substrate while the underfill material flows between the integrated circuit and the substrate.

BRIEF DESCRIPTION OF THE DRAWINGS

Figure 1 is a side view of an integrated circuit package of the prior art;

Figure 2 is a top view of an embodiment of an integrated circuit package of the present invention;

Figure 3 is an enlarged side view of the integrated circuit package;

Figure 4 is a schematic showing a process for assembling the integrated circuit package.

DETAILED DESCRIPTION OF THE INVENTION

Referring to the drawings more particularly by reference numbers, Figures 2 and 3 show an embodiment of an integrated circuit package 10 of the present invention. The package 10 may include a substrate 12 which has a first surface 14 and a second opposite surface 16. An integrated circuit 18 may be attached to the first surface 14 of the substrate 12 by a plurality of solder bumps 20. The solder bumps 20 may be arranged in a two-dimensional array across the integrated circuit 18. The solder bumps 20 may be attached to the integrated circuit 18 and to the

-5-

substrate 12 with a process commonly referred to as controlled collapse chip connection (C4).

The solder bumps 20 may carry electrical current between the integrated circuit 18 and the substrate 12. In one embodiment the substrate 12 may include an organic dielectric material. The package 10 may include a plurality of solder balls 22 that are attached to the second surface 16 of the substrate 12. The solder balls 22 can be reflowed to attach the package 10 to a printed circuit board (not shown).

The substrate 12 may contain routing traces, power/ground planes, vias, etc. which electrically connect the solder bumps 20 on the first surface 14 to the solder balls 22 on the second surface 16. The integrated circuit 18 may be encapsulated by an encapsulant (not shown). Additionally, the package 10 may incorporate a thermal element (not shown) such as a heat slug or a heat sink to remove heat generated by the integrated circuit 18.

The package 10 may include a first underfill material 24 that is attached to the integrated circuit 18 and the substrate 12. The package 10 may also include a second underfill material 26 which is attached to the substrate 12 and the integrated circuit 18. The second underfill material 26 may form a circumferential fillet that surround and seal the edges of the IC and the first underfill material 24. The sealing function of the second material 26 may inhibit

-6-

moisture migration, cracking of the integrated circuit and cracking of the first underfill material.

The first underfill material 24 may be an epoxy produced by Shin-Itsu of Japan under the product designation Semicoat 5230-JP. The Semicoat 5230-JP material provides favorable flow and adhesion properties. The second underfill material 26 may be an anhydride epoxy produced by Shin-Itsu under the product designation Semicoat 122X. The Semicoat 122X material has lower adhesion properties than the Semicoat 5230-JP material, but much better fracture/crack resistance.

Figure 4 shows a process for assembling the package 10. The substrate 12 may be initially baked in an oven 28 in step 1 to remove moisture from the substrate material. The substrate 12 is preferably baked at a temperature greater than the process temperatures of the remaining underfill process steps to insure that moisture is not released from the substrate 12 in the subsequent steps. By way of example, the substrate 12 may be baked at 163 degrees centigrade (°C).

After the baking process, the integrated circuit 18 may be mounted to the substrate 12. The integrated circuit 18 is typically mounted by reflowing the solder bumps 20.

The first underfill material 24 may be dispensed onto the substrate 12 along one side of the integrated circuit 18 at a first dispensing station 30. The first underfill material 24 may flow between the integrated

-7-

circuit 18 and the substrate 12 under a wicking action. By way of example, the first underfill material 24 may be dispensed at a temperature between 110 to 120°C. There may be a series of dispensing steps to fully fill the space between the integrated circuit 18 and the substrate 12.

The package 10 may be moved through an oven 32 to complete a flow out and partial gel of the first underfill material 24. By way of example, the underfill material 24 may be heated to a temperature of 120-145°C in the oven 32 to partially gel the underfill material 24. Partial gelling may reduce void formation and improve the adhesion between the integrated circuit 18 and the underfill material 24. The improvement in adhesion may decrease moisture migration and delamination between underfill material 24 and the IC 18 as well as delamination between underfill material 24 and the substrate 12. The reduction in void formation may decrease the likelihood of bump extrusion during thermal loading. The package may be continuously moved through the oven 32 which heats the underfill material during the wicking process. Continuously moving the substrate 12 during the wicking process decreases the time required to underfill the integrated circuit and thus reduces the cost of producing the package. The substrate can be moved between stations 30 and 34 and through the oven 32 on a conveyer (not shown).

-8-

The second underfill material 26 may be dispensed onto the substrate 12 along all four sides of the integrated circuit 18 at a second dispensing station 34. The second material 26 may be dispensed in a manner which creates a fillet that encloses and seals the first material 24. By way of example, the second underfill material 26 may be dispensed at a temperature of approximately 80 to 120°C.

The first 24 and second 26 underfill materials may be cured into a hardened state. The materials may be cured at a temperature of approximately 150 °C. After the underfill materials 24 and 26 are cured, solder balls 22 may be attached to the second surface 16 of the substrate 12.

While certain exemplary embodiments have been described and shown in the accompanying drawings, it is to be understood that such embodiments are merely illustrative of and not restrictive on the broad invention, and that this invention not be limited to the specific constructions and arrangements shown and described, since various other modifications may occur to those ordinarily skilled in the art.

CLAIMS

What is claimed is:

1. A process line for underfilling an integrated circuit that is mounted to a substrate, comprising:
a first dispensing station that can dispense a first underfill material onto the substrate; and,
an oven that heats the first underfill material, said oven moves said substrate while said first underfill material flows between the integrated circuit and the substrate.

2. The process line as recited in claim 1, further comprising a second dispensing station which dispenses a second underfill material onto the substrate.

3. The process line as recited in claim 1, wherein said second underfill material seals said first underfill material.

4. The process line as recited in claim 1, wherein said first underfill material is an epoxy.

5. The process line as recited in claim 4, wherein said second underfill material is an anhydride epoxy.

-10-

6. The process line as recited in claim 1, wherein said oven heats said first underfill material to a partial gel state.

7. A process for underfilling an integrated circuit that is mounted to a substrate, comprising:
dispensing a first underfill material onto the substrate; and,

heating the first underfill material while moving the substrate through an oven.

8. The process as recited in claim 7, wherein said first underfill material flows between the integrated circuit and the substrate.

9. The process as recited in claim 8, further comprising the step of dispensing a second underfill material around the first underfill material.

10. The process as recited in claim 7, further comprising the step of heating the substrate before the first underfill material is dispensed.

11. The process as recited in claim 10, wherein the substrate is heated to a temperature that is greater than the temperature of the first underfill material moving through the oven.

-11-

12. The process as recited in claim 7, further comprising the step of mounting the integrated circuit to the substrate with a solder bump.

13. The process as recited in claim 12, further comprising the step of attaching a solder ball to the substrate.

14. A process for underfilling an integrated circuit that is mounted to a substrate, comprising:
dispensing a first underfill material onto the substrate; and,

moving the substrate while the first underfill material flows between the integrated circuit and the substrate.

15. The process as recited in claim 14, further comprising the step of dispensing a second underfill material around the first underfill material.

16. The process as recited in claim 14, further comprising the step of heating the substrate before the first underfill material is dispensed.

17. The process as recited in claim 14, further comprising the step of mounting the integrated circuit to the substrate with a solder bump. 18. The process

-12-

as recited in claim 17, further comprising the step of attaching a solder ball to the substrate.

1/2

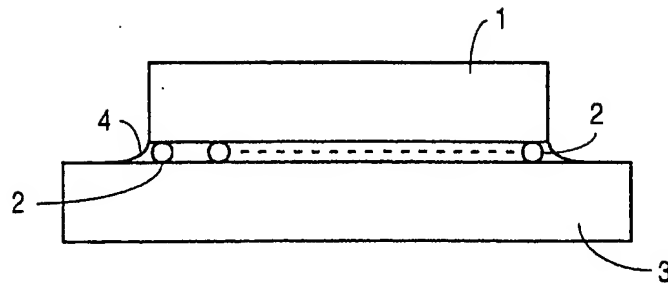


FIG. 1
(PRIOR ART)

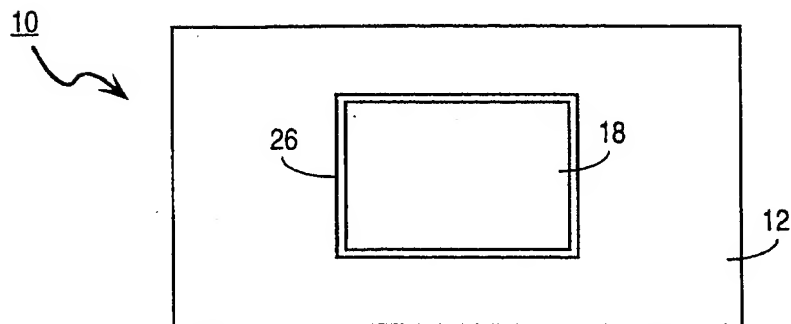


FIG. 2

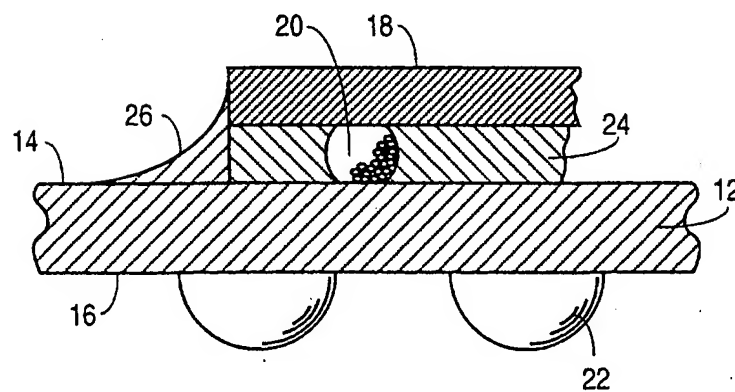
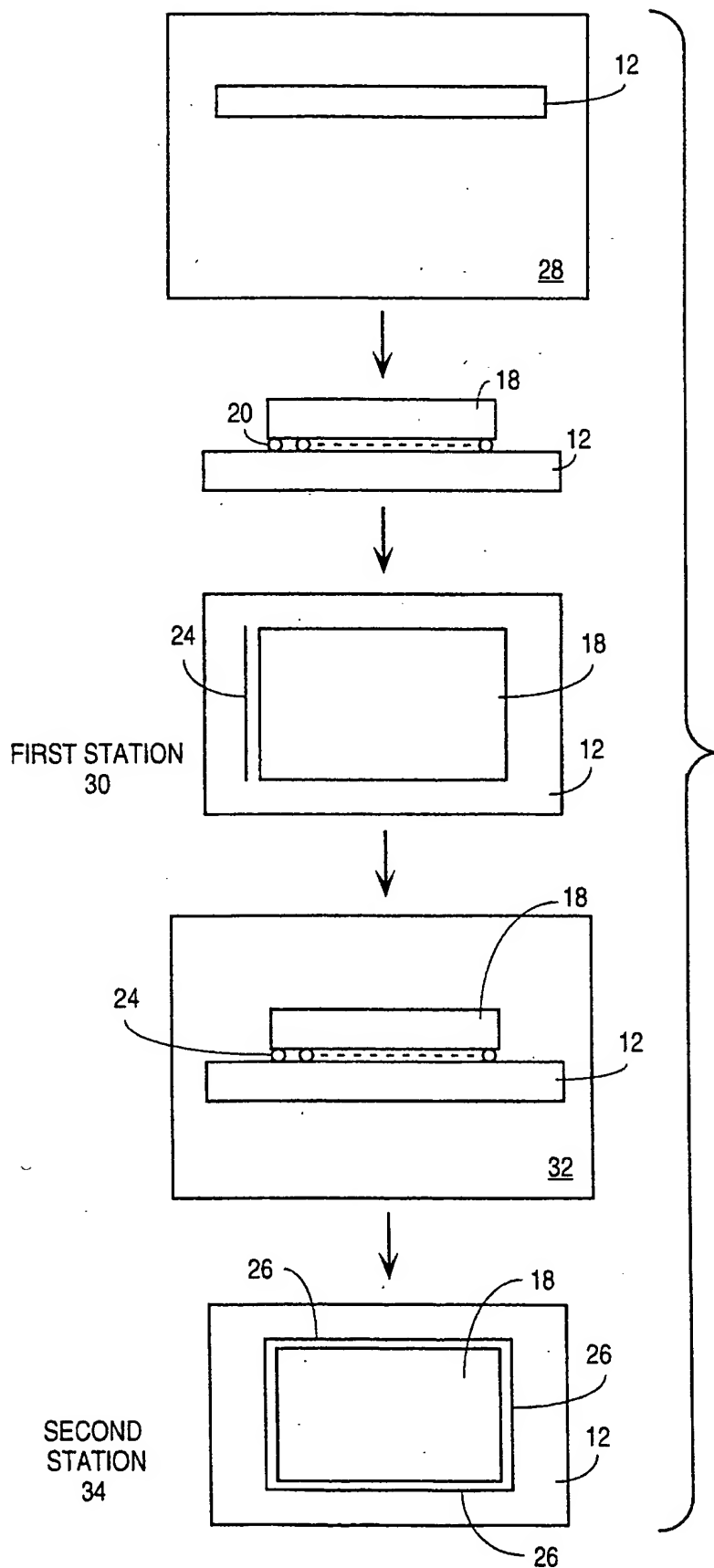


FIG. 3

2/2



SUBSTITUTE SHEET (RULE 26)

FIG. 4

INTERNATIONAL SEARCH REPORT

Int. . Jonal Application No

PCT/US 00/03243

A. CLASSIFICATION OF SUBJECT MATTER

IPC 7 H01L21/56 H01L23/18 H01L23/24

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

IPC 7 H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	DATABASE WPI Section EI, Week 199827 Derwent Publications Ltd., London, GB; Class U11, AN 1998-303605 XP002136126 -& JP 10 107082 A (NEC CORP), 24 April 1998 (1998-04-24)	7,8,12, 13
A	abstract; figures 4,5,8,9	1-6, 9-11, 14-18
P,X	-& US 5 981 313 A (TANAKA KEI) 9 November 1999 (1999-11-09) figures 4,5,8,9 column 5, line 21 -column 6, line 3 column 7, line 17 -column 8, line 7	7,8,12, 13
P,A		1-6, 9-11, 14-18

-/--

☒ Further documents are listed in the continuation of box C.

☒ Patent family members are listed in annex.

* Special categories of cited documents :

"A" document defining the general state of the art which is not considered to be of particular relevance

"E" earlier document but published on or after the international filing date

"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)

"O" document referring to an oral disclosure, use, exhibition or other means

"P" document published prior to the international filing date but later than the priority date claimed

"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention

"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art.

"&" document member of the same patent family

Date of the actual completion of the international search

20 April 2000

Date of mailing of the international search report

03/05/2000

Name and mailing address of the ISA

European Patent Office, P.B. 5818 Patentlaan 2
NL - 2280 HV Rijswijk
Tel. (+31-70) 340-2040, Tx. 31 651 epo nl,
Fax: (+31-70) 340-3016

Authorized officer

Polesello, P

INTERNATIONAL SEARCH REPORT

International Application No

PCT/US 00/03243

C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No. *
A	EP 0 340 492 A (IBM) 8 November 1989 (1989-11-08) figure 3 column 5, line 27 - line 46 column 8, line 14 -column 15, line 46 -----	1-18
A	US 5 864 178 A (MORI MIKI ET AL) 26 January 1999 (1999-01-26) figures 11-17 column 5, line 41 - line 63 column 6, line 50 -column 7, line 42 column 21, line 33 -column 25, line 26 column 28, line 57 -column 29, line 27 -----	1-18
A	LACHANCE R ET AL: "CORROSION/MIGRATION STUDY OF FLIP CHIP UNDERFILL AND CERAMIC OVERCOATING" PROCEEDINGS OF THE ELECTRONIC COMPONENTS AND TECHNOLOGY CONFERENCE,US,NEW YORK, NY: IEEE,1997, pages 885-889, XP000803846 ISBN: 0-7803-3858-8 figures 1.0,2.0 paragraphs 'INTRODUCTION!','CONCLUSION!' -----	1-18
A		3,5,7-16
A	US 5 629 566 A (DOI KAZUhide ET AL) 13 May 1997 (1997-05-13) figures 2,4-10 column 3, line 22 -column 4, line 14 column 5, line 38 - line 49 column 7, line 22 -column 9, line 10 -----	1,3,4,7, 12-15, 17,18

INTERNATIONAL SEARCH REPORT

Information on patent family members

International Application No

PCT/US 00/03243

Patent document cited in search report	Publication date	Patent family member(s)	Publication date
JP 10107082 A	24-04-1998	JP 2848357 B US 5981313 A	20-01-1999 09-11-1999
EP 0340492 A	08-11-1989	JP 1722939 C JP 2016756 A JP 4012027 B	24-12-1992 19-01-1990 03-03-1992
US 5864178 A	26-01-1999	JP 8195414 A JP 9017914 A JP 9036177 A JP 9064097 A JP 9172110 A US 5959363 A	30-07-1996 17-01-1997 07-02-1997 07-03-1997 30-06-1997 28-09-1999
US 5629566 A	13-05-1997	JP 8055938 A	27-02-1996

